SONY

Ver.1.0

IMX515-AAQN

Diagonal 6.43 mm (Type 1/2.8) CMOS Solid-state Image Sensor with Square Pixel for Color Cameras

Description

The IMX515-AAQN is a diagonal 6.4 mm (Type 1/2.8) CMOS active pixel type solid-state image sensor with a square pixel array and 8.46 M effective pixels. This chip operates with analog 2.9 V, digital 1.1 V, and interface 1.8 V triple power supply, and has low power consumption. High sensitivity, low dark current and no smear are achieved through the adoption of R, G and B primary color mosaic filters. This chip features an electronic shutter with variable charge-integration time.

(Applications: Security cameras, FA cameras, Industrial cameras)

Features

- ◆ CMOS active pixel type dots
- ◆ Built-in timing adjustment circuit, H/V driver and serial communication circuit
- ♦ Input frequency: 24 MHz / 27 MHz / 37.125 MHz / 72 MHz / 74.25 MHz
- ♦ Number of recommended recording pixels: 3840 (H) × 2160 (V) approx. 8.29 M pixels
- ◆ Readout mode

All-pixel scan mode

Horizontal / Vertical 2/2-line binning mode

Window cropping mode

Horizontal / Vertical direction - Normal / Inverted readout mode

◆ Readout rate

Maximum frame rate in

All-pixel scan mode: 12 bit: 52.2 frame/s, 10 bit: 61.6 frame/s

◆ High dynamic range (HDR) function

Multiple exposure HDR

Digital overlap HDR

- ◆ Synchronizing sensors function
- ◆ Variable-speed shutter function (resolution 1H units)
- ◆ CDS / PGA function

0 dB to 30 dB: Analog Gain 30 dB (step pitch 0.3 dB)

30.3 dB to 72 dB: Analog Gain 30 dB + Digital Gain 0.3 dB to 42 dB (step pitch 0.3 dB)

◆ Supports I/O

CSI-2 serial data output (2 Lane / 4 Lane), RAW10 / RAW12 output



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Device Structure

◆ CMOS image sensor

♦ Image size Diagonal 6.4 mm (Type 1/2.8) approx. 8.40 M pixels, All pixels

◆ Total number of pixels
♦ Number of effective pixels
♦ Number of active pixels
♦ Number of active pixels
♦ Number of recommended recording pixels
3864 (H) × 2192 (V) approx. 8.46 M pixels
♦ Number of recommended recording pixels
3840 (H) × 2160 (V) approx. 8.29 M pixels

♦ Unit cell size 1.45 μm (H) × 1.45 μm (V)

♦ Optical black Horizontal (H) direction: Front 0 pixel, rear 0 pixel

Vertical (V) direction: Front 36 pixels, rear 0 pixel

◆ Dummy Horizontal (H) direction: Front 0 pixel, rear 0 pixel

Vertical (V) direction: Front 1 pixel, rear 1 pixel

◆ Package 65 pin BGA

Image Sensor Characteristics

(Tj = 60 °C)

ltem		Value	Remarks	
Sensitivity (F5.6)	Тур.	5640 Digit/lx/s	12 bit converted value	
Saturation signal	Min.	3895 Digit	12 bit converted value	

Basic Drive Mode

Drive mode	Recommended number of recording pixels	Maximum frame rate [frame/s]	Output interface	ADC [bit]
All pixel	3840 (H) × 2160 (V) approx. 8.29 M pixels	61.6	CSI-2	10
Horizontal/ Vertical 2/2-line binning	1920 (H) × 1080 (V) approx. 2.07 M pixels	88.1	CSI-2	10

